

In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended.

1. (Currently Amended) An integrated circuit including  
a patterned copper layer,  
a patterned aluminum layer,  
~~a stud connection in an opening in a layer of~~  
~~material, said opening extending between a location on~~  
~~said patterned copper layer and a location on said~~  
~~patterned aluminum layer, said stud connection being~~  
~~formed of tungsten, and~~  
a liner in said opening and having a thickness,  
said liner extending between said ~~stud connection~~  
patterned aluminum layer and said patterned copper  
layer at said location on said patterned copper layer,  
and  
a stud connection formed of tungsten and located  
within said liner.
2. (Original) An integrated circuit as recited in  
claim 1 wherein said liner comprises  
a layer of tantalum nitride, and  
a layer of PVD tungsten.
3. (Original) An integrated circuit as recited in  
claim 1 wherein said liner comprises  
a layer of titanium, and  
a layer of titanium nitride or PVD tungsten.
4. (Cancelled)
5. (Original) An integrated circuit as recited in  
claim 1 wherein said patterned aluminum layer includes  
a layer of at least one of titanium and titanium  
nitride.

6. (Original) An integrated circuit as recited in claim 2 wherein said patterned aluminum layer includes a layer of at least one of titanium and titanium nitride.

7. (original) An integrated circuit as recited in claim 3 wherein said patterned aluminum layer includes a layer of at least one of titanium and titanium nitride.

8. (Cancelled)

9. (Original) An integrated circuit as recited in claim 1, further including a covering layer.

10. (Original) An integrated circuit as recited in claim 9 wherein said covering layer includes a layer of silane-based high density plasma oxide.

11. - 16. (Withdrawn)